TNMNM55H

100V N-Channel MOSFETs

BV_{DSS}	$R_{DS(ON)}$	I_D
100 V	5.5 Ω	300 mA

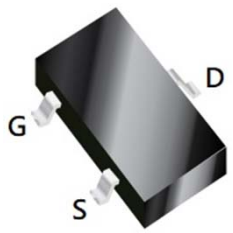
General Description

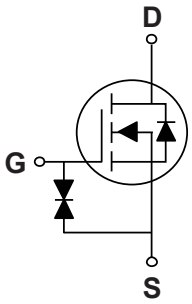
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

- $R_{DS(ON)} \leqq 5.5\Omega @ V_{GS}=10V$
- Improved dv/dt Capability
- Fast Switching
- Green Device Available
- G-S ESD Protection Diode Embedded
- ESD protected up to 2KV

SOT-23 Pin Configuration





Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-Held Instruments

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current - Continuous (T_A=25°C)	300	mA
I_{DM}	Drain Current - Pulsed (NOTE 1)	1.2	A
P_D	Power Dissipation (T_A=25°C)	1.56	W
T_J	Operating Junction Temperature Range	-55 to 150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
Marking Code		a	

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	80	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±20	uA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=0.15A	---	---	5.5	Ω
		V_{GS}=4.5V , I_D=0.12A	---	---	6.5	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=250uA	1.5	---	3.0	V

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	V_{DS}=80V , V_{GS}=0V , f=1MHz	---	60	---	pF
C_{oss}	Output Capacitance		---	18	---	
C_{rss}	Reverse Transfer Capacitance		---	5.2	---	

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	0.3	A
I_{SM}	Pulsed Source Current		---	---	0.6	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=0.2A	---	---	1	V
T_{rr}	Reverse Recovery Time	V_R=100V , I_S=0.1A , di/dt=100A/us	---	8.5	---	nS
Q_{rr}	Reverse Recovery Charge		---	5.8	---	nC

NOTES：

1. Repetitive Rating：Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

Characteristics Curves

FIG. 1-I_D vs T_C

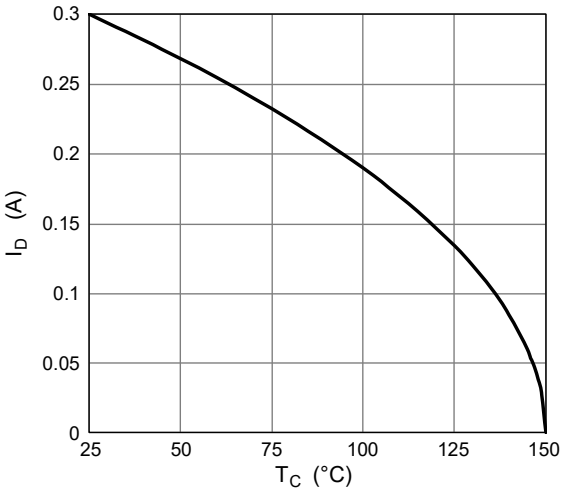


FIG. 2-Normalized $R_{DS(ON)}$ vs T_J

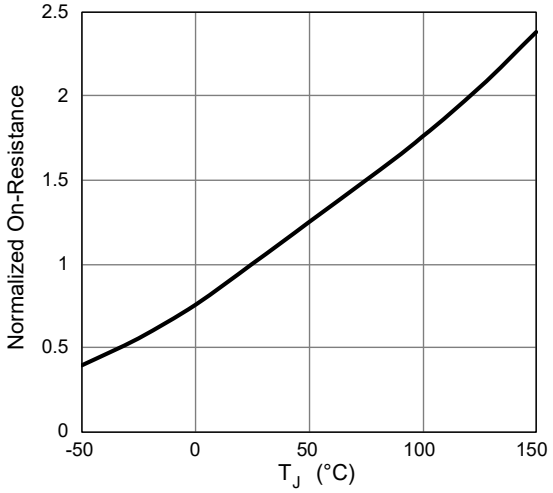


FIG. 3-Normalized V_{th} vs T_J

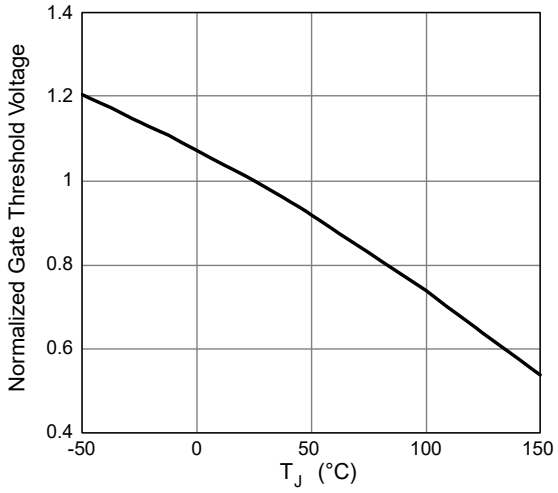


FIG. 4-$R_{DS(ON)}$ vs I_D

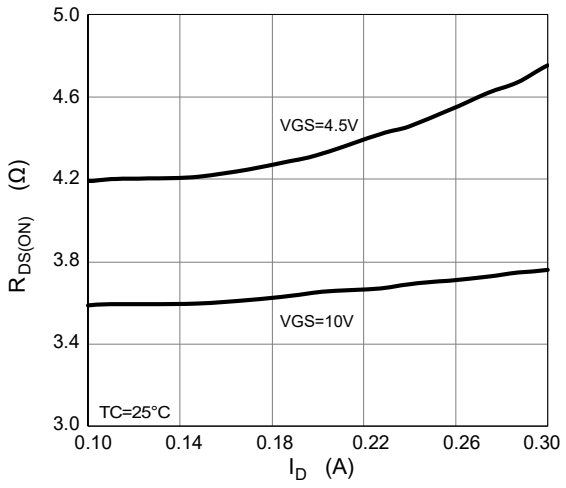


FIG. 5-Normalized Transient Impedance

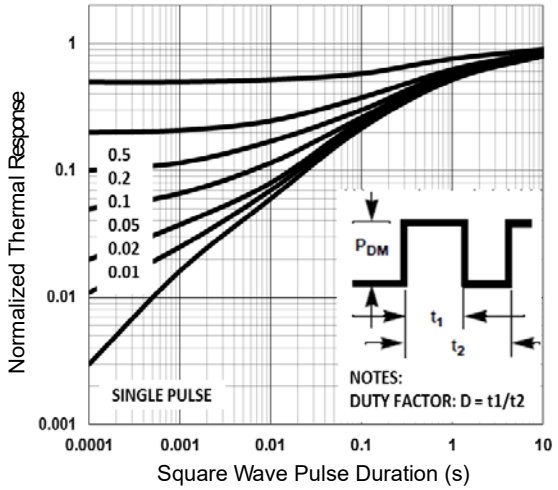
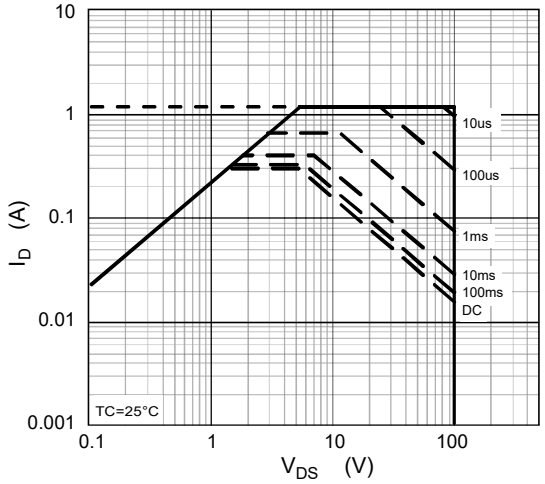
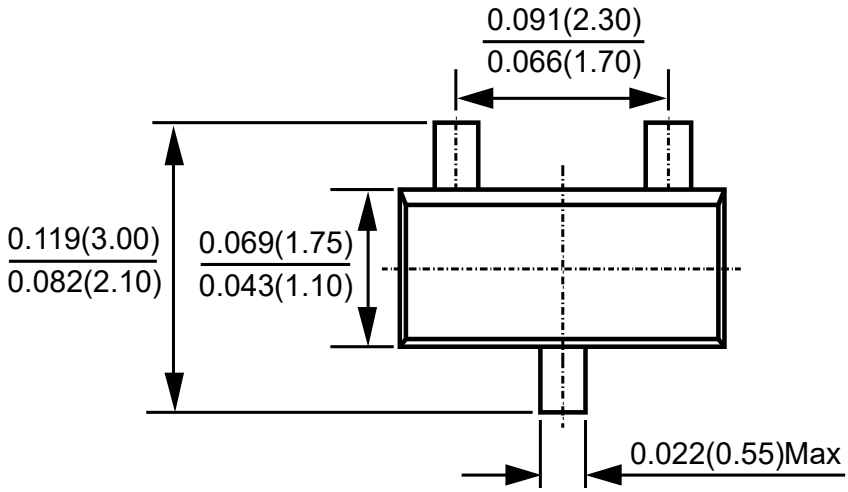
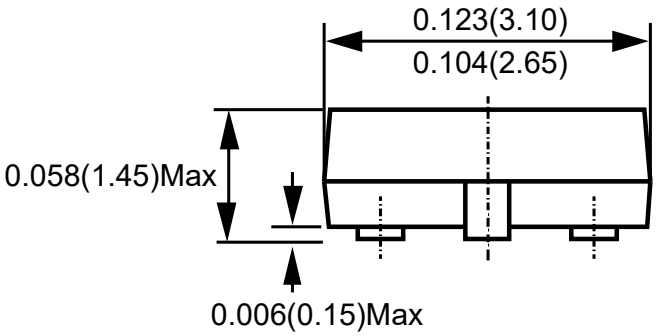


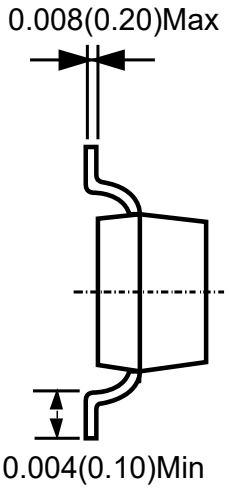
FIG. 6-Maximum Safe Operation Area



Package Outline Dimensions







SOT-23

Dimensions in inches and (millimeters)

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